



STPS1045D/F

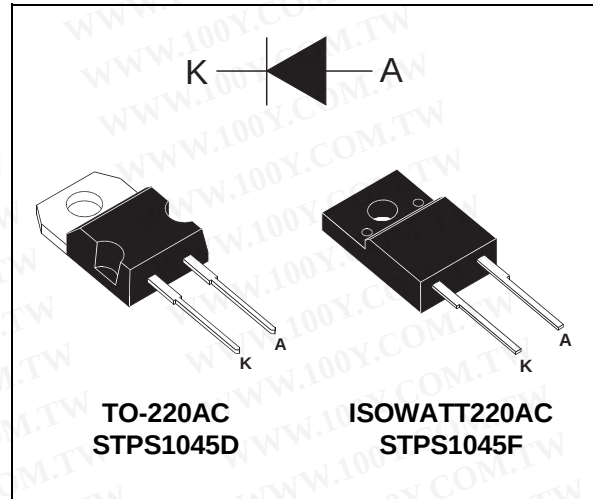
POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_F(AV)$	10 A
V_{RRM}	45 V
V_F	0.57 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- INSULATED PACKAGE: ISOWATT220AC
Insulating voltage = 2000V DC
Capacitance = 12pF



DESCRIPTION

Single chip Schottky rectifier suited for Switch Mode Power Supply and high frequency DC to DC converters.

This device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			45	V
$I_{F(RMS)}$	RMS forward current			30	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AC	$T_c = 150^\circ\text{C}$	10	A
		ISOWATT220AC	$T_c = 145^\circ\text{C}$		
I_{FSM}	Surge non repetitive forward current		$t_p = 10 \text{ ms}$ Sinusoidal	180	A
I_{RRM}	Repetitive peak reverse current		$t_p = 2 \mu\text{s}$ $F = 1\text{KHz}$	1	A
T_{stg}	Storage temperature range			- 65 to + 175	$^\circ\text{C}$
T_j	Maximum junction temperature			175	$^\circ\text{C}$
dV/dt	Critical rate of rise of reverse voltage			10000	V/ μs

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	TO-220AC	2.2	°C/W
		ISOWATT220AC	4.5	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			100	μA
		T _j = 125°C				15	mA
V _F **	Forward voltage drop	T _j = 25°C	I _F = 15 A			0.84	V
		T _j = 125°C	I _F = 15 A			0.72	
		T _j = 125°C	I _F = 7.5 A			0.57	

Pulse test : * tp = 5 ms, δ < 2 %
 ** tp = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation :
 $P = 0.42 \times I_{F(AV)} + 0.015 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current.

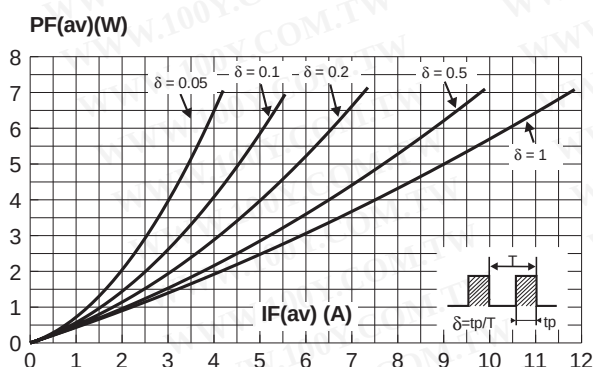


Fig. 2: Average current versus ambient temperature (δ : 0.5).

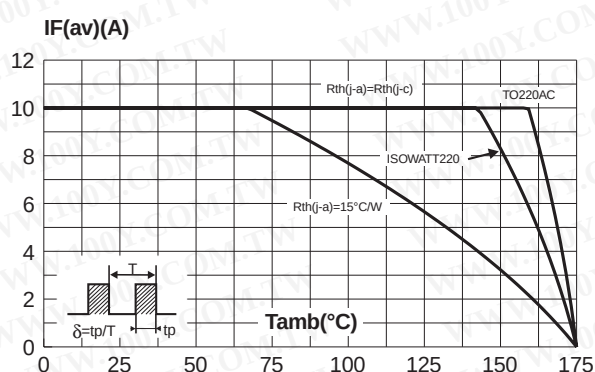


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values) (TO-220AC).

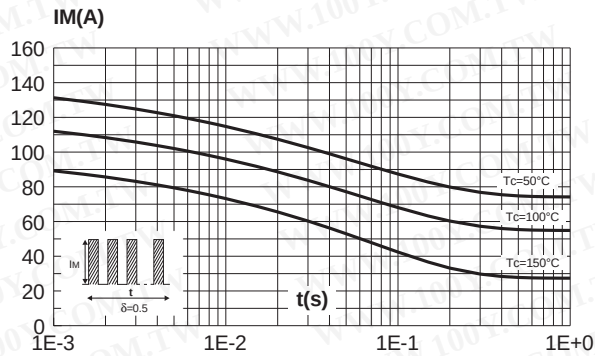


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values) (ISOWATT220AC).

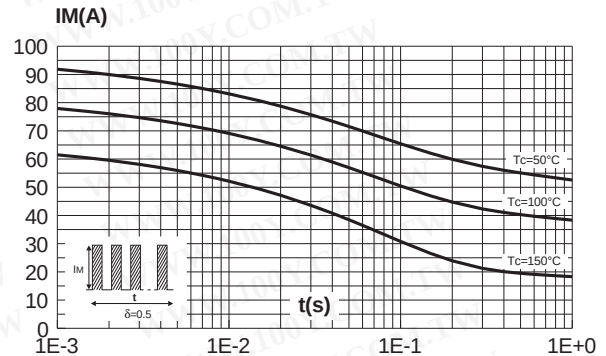


Fig. 4-1: Relative variation of thermal transient impedance junction to case versus pulse duration (TO-220AC).

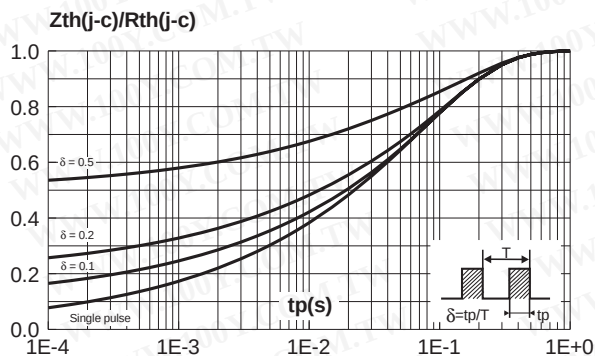


Fig. 4-2: Relative variation of thermal transient impedance junction to case versus pulse duration (ISOWATT220AC).

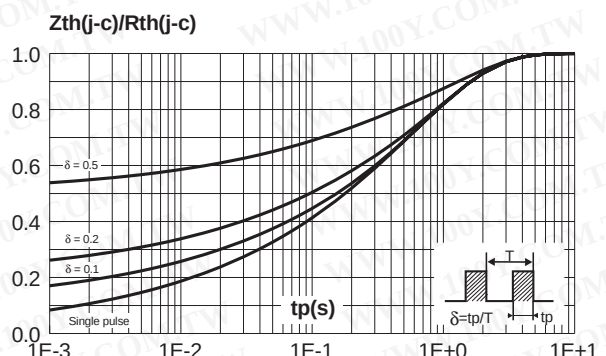


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values).

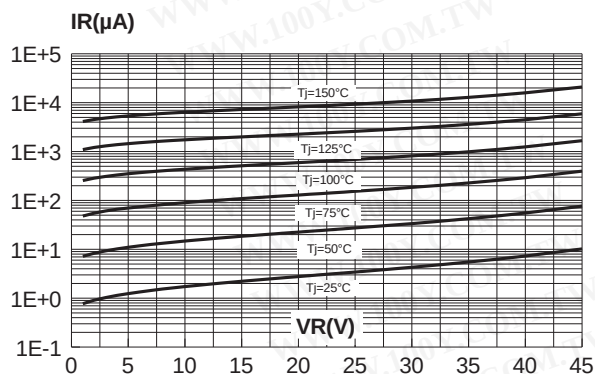
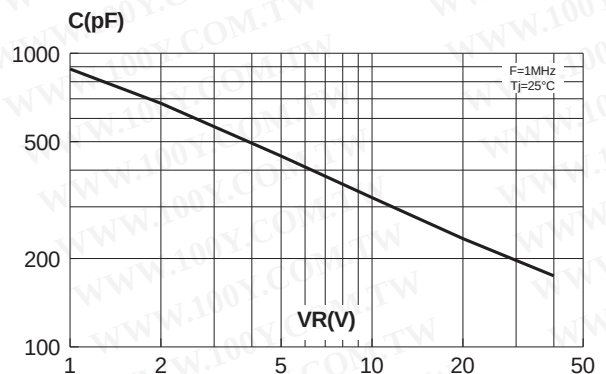
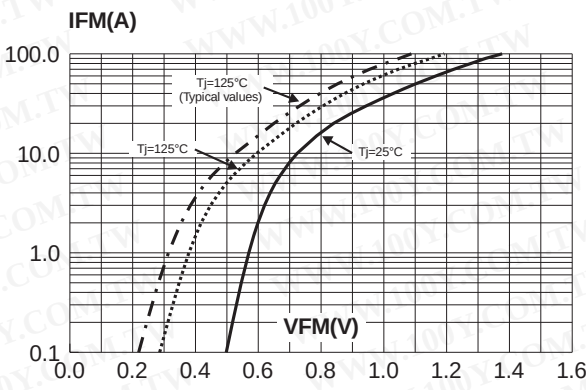


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

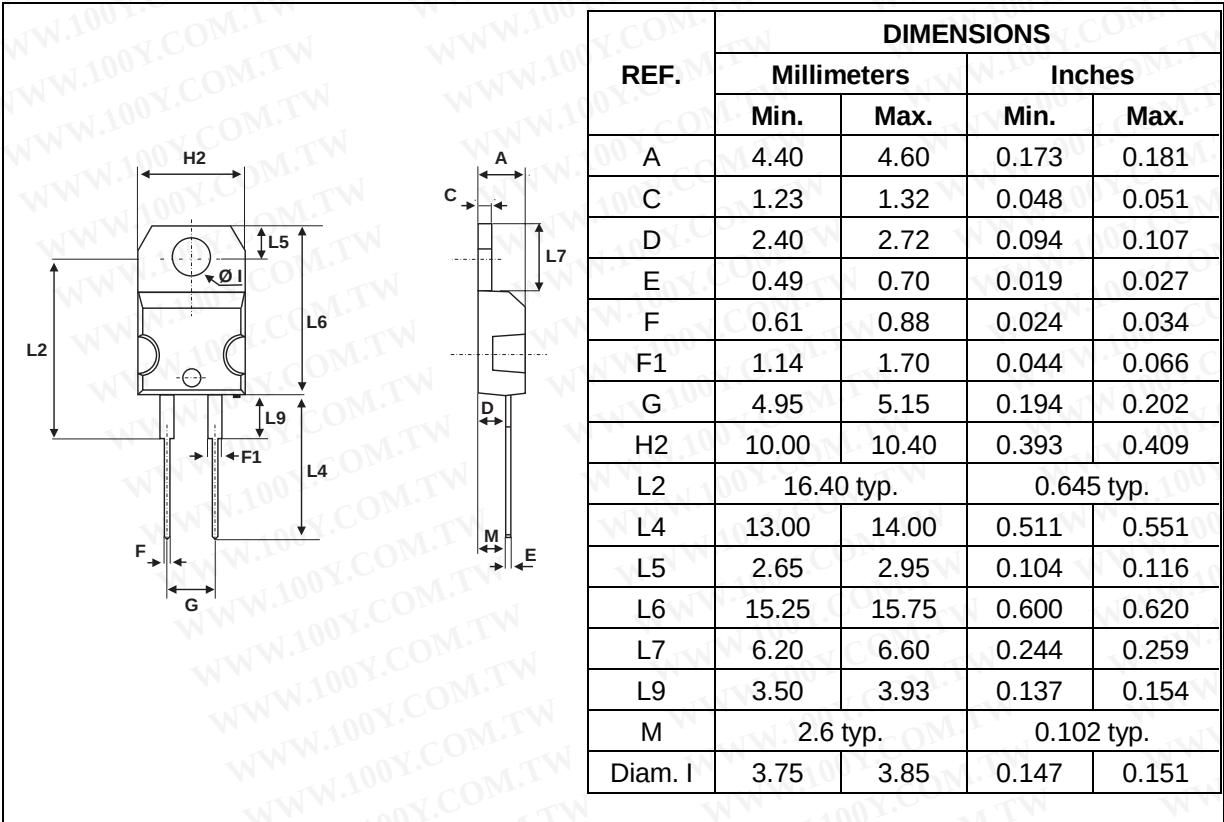


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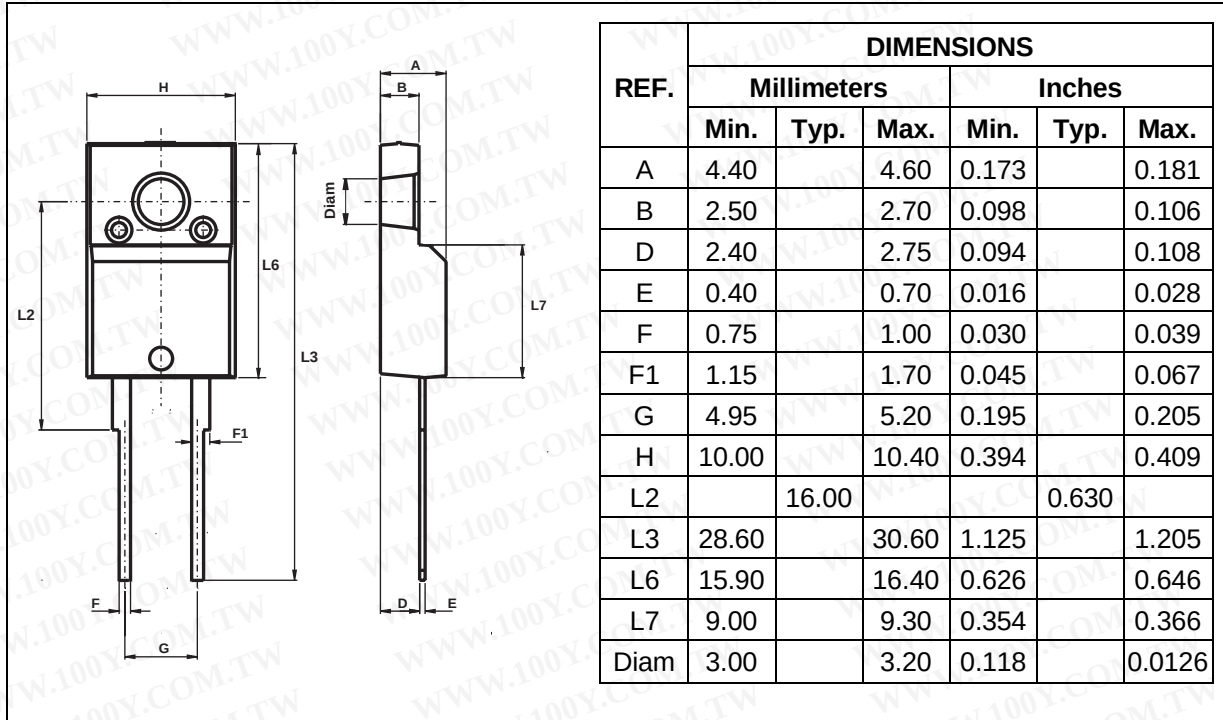
Fig. 7: Forward voltage drop versus forward current (maximum values).



PACKAGE MECHANICAL DATA
TO-220AC



PACKAGE MECHANICAL DATA
ISOWATT220AC



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